

3SK303(Tentative), 3SK307(Tentative)

Silicon N-Channel MOS

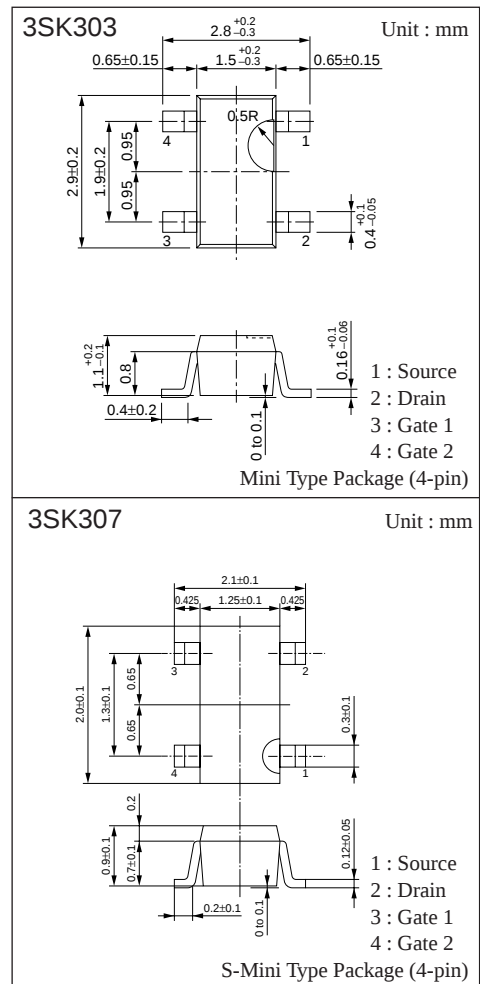
For VHF amplification

■ Features

- Though low voltage operation, performance is equivalent to the conventional product.
- Downsizing of sets by mini or S-mini type package, and automatic insertion by taping/magazine packing are available.

■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source voltage	V _{DS}	15	V
Gate 1-Source voltage	V _{G1S}	±8	V
Gate 2-Source voltage	V _{G2S}	±8	V
Drain current	I _{DS}	30	mA
Allowable power dissipation	P _D	150	mW
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	– 55 to +150	°C



■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain current	I _{DS}	V _{DS} =10V, V _{G1S} =1V, V _{G2S} = 3V	0	3	10	mA
Gate 1 cut-off current	I _{G1SS}	V _{DS} = V _{G2S} = 0, V _{G1S} = ±8V			±20	nA
Gate 2 cut-off current	I _{G2SS}	V _{DS} =V _{G2S} = 0, V _{G1S} = ±8V			±20	nA
Gate 1-Source cut-off voltage	V _{G1SC}	V _{DS} =10V, V _{G2S} = 4V, I _{DS} =100μA	0	0.7	1	V
Gate 2-Source cut-off voltage	V _{G2SC}	V _{DS} =10V, V _{G2S} = 4V, I _{DS} =100μA	0.2	0.7	1.2	V
Drain-Source voltage	V _{DSX}	I _{DS} =50μA, V _{G1S} = – 5V, V _{G2S} = 0	15			V
Forward transadmittance	Y _{fs}	V _{DS} =10V, I _{DS} =10mA, V _{G2S} = 3V	18	22	28	mS
Input capacitance	C _{iss}	V _{DS} =10V, V _{G1S} = V _{G2S} = –5V, f=1MHz	2	2.4	3.2	pF
Output capacitance	C _{oss}		0.7	1	1.3	pF
Feedback capacitance	C _{rss}			0.02		pF
Power gain	PG	V _{DS} = 8V, I _{DS} = 8mA, V _{G2S} = 3V, f= 200MHz	19	23	28	dB
Noise figure	NF			2.3	3.2	dB

■ Marking

